



# N-Channel 60 V (D-S) MOSFET



PRODUCT SUMMARY			
V <sub>DS</sub> (V)	60		
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 10 \text{ V}$	0.0022		
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 7.5 \text{ V}$	0.0024		
Q <sub>g</sub> typ. (nC)	128		
I <sub>D</sub> (A)	120 <sup>d</sup>		
Configuration	Single		

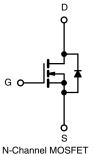
#### **FEATURES**

- TrenchFET® power MOSFET
- Maximum 175 °C junction temperature
- Q<sub>gd</sub>/Q<sub>gs</sub> ratio < 0.25
- Operable with logic-level gate drive
- 100 % R<sub>g</sub> and UIS tested
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>



### **APPLICATIONS**

- Power supply
- Secondary synchronous rectification
- DC/DC converter
- Power tools
- · Motor drive switch
- DC/AC inverter
- Battery management



ORDERING INFORMATION	
Package	TO-263
Lead (Pb)-free and halogen-free	SUM50020E-GE3

ABSOLUTE MAXIMUM RATINGS	(T <sub>C</sub> = 25 °C, unless other	rwise noted)		
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V <sub>DS</sub>	60	v
Gate-source voltage		V <sub>GS</sub>	± 20	
Continuous drain surrent (T. 150 °C)	T <sub>C</sub> = 25 °C		120 <sup>d</sup>	
Continuous drain current (T <sub>J</sub> = 150 °C)	T <sub>C</sub> = 70 °C	I <sub>D</sub>	120 <sup>d</sup>	Α
Pulsed drain current (t = 100 µs)		I <sub>DM</sub>	300	A
Avalanche current	L = 0.1 mH	I <sub>AS</sub>	75	
Single avalanche energy <sup>a</sup>	L=0.11IIII	E <sub>AS</sub>	281	mJ
Maximum nawar dissination 3	T <sub>C</sub> = 25 °C	В	375 <sup>b</sup>	W
Maximum power dissipation <sup>a</sup>	T <sub>C</sub> = 125 °C	$ P_D$	125 <sup>b</sup>	] vv
Operating junction and storage temperature ra	inge	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C

ERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-ambient (PCB mount) <sup>c</sup>	R <sub>thJA</sub>	40	°C/W
Junction-to-case (drain)	R <sub>thJC</sub>	0.4	C/VV

### Notes

- a. Duty cycle ≤ 1 %
- b. See SOA curve for voltage derating
- c. When mounted on 1" square PCB (FR4 material)
- d. Package limited



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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static				•		
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS}$ = 0 V, $I_D$ = 250 $\mu A$	60	-	-	V
Gate threshold voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS},I_D=250\;\mu A$	2	-	4	V
Gate-body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 250	nΑ
		V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V	-	-	1	
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C	-	-	150	μA
		V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C	-	-	5	mA
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	120	-	-	Α
Duelle designed and address of the con-		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 30 A	-	0.0018	0.0022	
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 7.5 \text{ V}, I_D = 20 \text{ A}$	-	0.0020	0.0024	Ω
Forward transconductance <sup>a</sup>	9 <sub>fs</sub>	$V_{DS} = 15 \text{ V}, I_D = 30 \text{ A}$	-	145	-	S
Dynamic <sup>b</sup>				1		
Input capacitance	C <sub>iss</sub>		-	11 150	-	
Output capacitance	Coss	$V_{GS} = 0 \text{ V}, V_{DS} = 30 \text{ V}, f = 1 \text{ MHz}$	-	4255	-	pF
Reverse transfer capacitance	C <sub>rss</sub>		-	420	-	
Total gate charge <sup>c</sup>	Qg		-	128	-	
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	-	44	-	nC
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>		-	9	-	
Gate resistance	$R_{g}$	f = 1 MHz	0.32	1.6	3.2	Ω
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>		-	18	36	
Rise time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 30 \text{ V}, R_L = 5 \Omega$	-	20	40	
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 10$ A, $V_{GEN} = 10$ V, $R_g = 1$ $\Omega$	-	55	100	ns
Fall time <sup>c</sup>	t <sub>f</sub>		-	23	35	
Drain-Source Body Diode Ratings a	nd Characteris	stics <sup>b</sup> (T <sub>C</sub> = 25 °C)				
Pulsed current (t = 100 μs)	I <sub>SM</sub>		-	-	300	Α
Forward voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = 10 A, V <sub>GS</sub> = 0 V	-	0.8	1.5	V
Reverse recovery time	t <sub>rr</sub>		-	120	180	ns
Peak reverse recovery charge	I <sub>RM(REC)</sub>	$I_F = 39 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$	-	5.5	11	Α
Reverse recovery charge	Q <sub>rr</sub>		-	0.320	0.480	μC

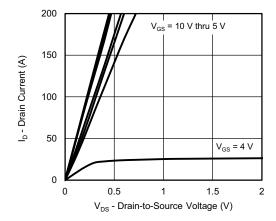
### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

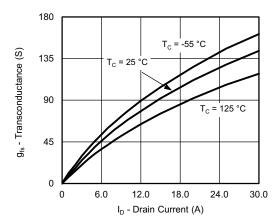
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



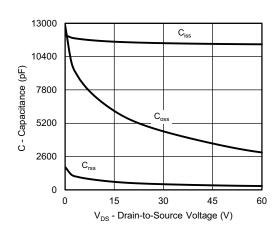
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



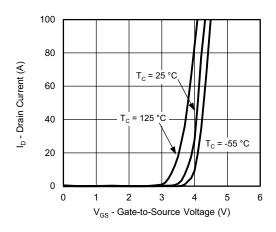
#### **Output Characteristics**



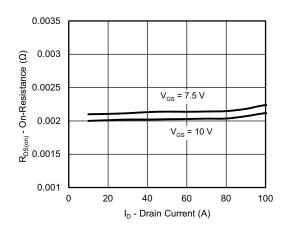
### Transconductance



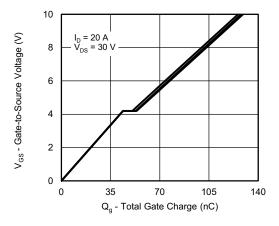
### Capacitance



### **Transfer Characteristics**



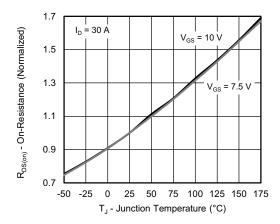
On-Resistance vs. Drain Current



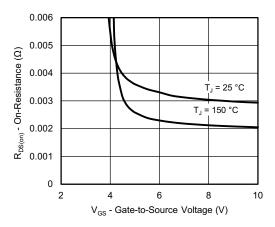
**Gate Charge** 



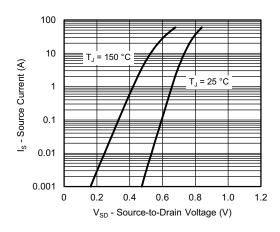
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



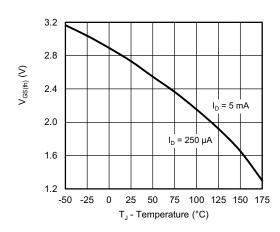
On-Resistance vs. Junction Temperature



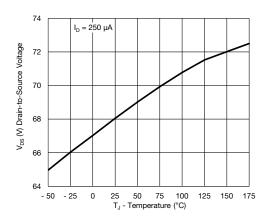
On-Resistance vs. Gate-to-Source Voltage



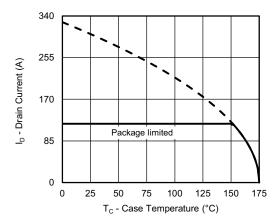
**Source Drain Diode Forward Voltage** 



**Threshold Voltage** 



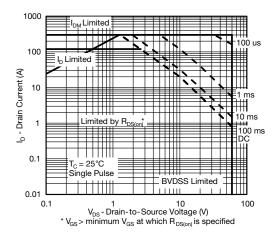
**Drain Source Breakdown vs. Junction Temperature** 

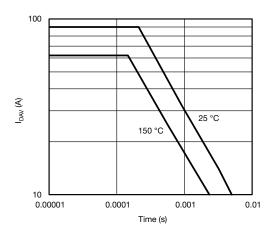


**Current De-rating** 



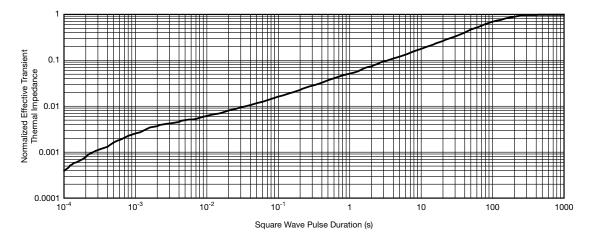
# **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)





Safe Operating Area

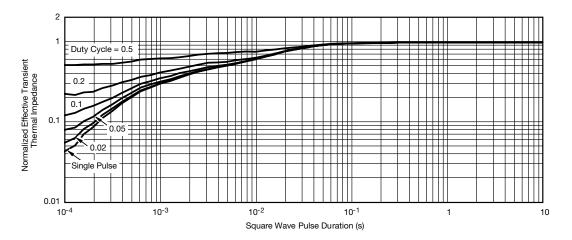
Single Pulse Avalanche Current Capability vs. Time



Normalized Thermal Transient Impedance, Junction-to-Ambient



## THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction to Case (25 °C)

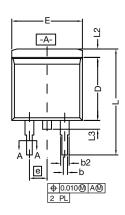
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

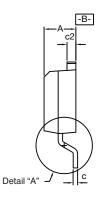
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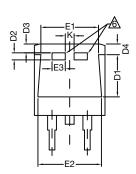
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# TO-263 (D<sup>2</sup>PAK): 3-LEAD

### **VERSION 1: FACILITY CODE = T**









**DETAIL A (ROTATED 90°)** 



≥ <u>↓</u>			ţ
< T		10	ပ
SF	CTION	1	1

### **Notes**

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. \*: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6. This feature is for thick lead.

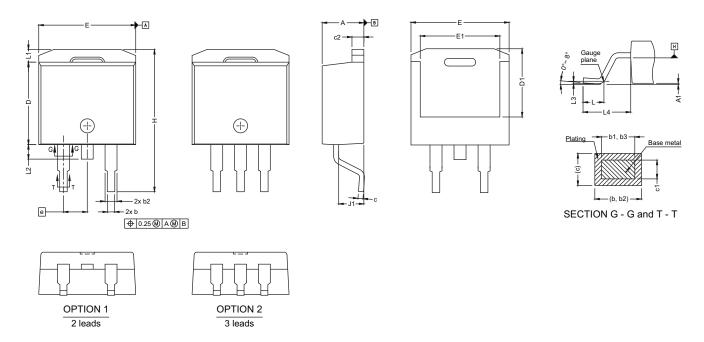
		INC	HES	MILLIN	METERS
	DIM.	MIN.	MAX.	MIN.	MAX.
	Α	0.160	0.190	4.064	4.826
	b	0.020	0.039	0.508	0.990
	b1	0.020	0.035	0.508	0.889
b2		0.045	0.055	1.143	1.397
C*	Thin lead	0.013	0.018	0.330	0.457
C	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
CI	Thick lead	0.023	0.027	0.584	0.685
	c2	0.045	0.055	1.143	1.397
	D	0.340	0.380	8.636	9.652
	D1	0.220	0.240	5.588	6.096
	D2	0.038	0.042	0.965	1.067
	D3	0.045	0.055	1.143	1.397
	D4	0.044	0.052	1.118	1.321
	E	0.380	0.410	9.652	10.414
	<u>E1</u>	0.245	-	6.223	-
	E2	0.355	0.375	9.017	9.525
	E3	0.072	0.078	1.829	1.981
	е 0.		) BSC	2.54	BSC
K		0.045	0.055	1.143	1.397
	L	0.575	0.625	14.605	15.875
	L1	0.090	0.110	2.286	2.794
	L2	0.040	0.055	1.016	1.397
	L3	0.050	0.070	1.270	1.778
	L4	0.010	BSC	0.254	BSC
	М	-	0.002	-	0.050



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### **VERSION 2: FACILITY CODE = N**



DIM.	MIN.	MAX.	
A	4.36	4.56	
A1	0	0.25	
b	0.70	0.90	
b1	0.51	0.89	
b2	1.20	1.46	
b3	1.17	1.37	
С	0.38	0.694	
c1	0.38	0.534	
c2	1.19	1.34	
D	8.60	9.00	
D1	6.9	7.5	
E	10.15	10.55	
E1	8.1	8.7	
е	2.54	BSC	
Н	15.0	15.6	
L	1.9	2.5	
L1	-	1.65	
L2	-	1.78	
L3	0.25	5 typ.	
L4	4.78	5.28	
J1	2.56	2.96	

DWG: 5843





### RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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